

P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
- 60	0.015 at $V_{GS} = - 10$ V	- 50 ^d
	0.020 at $V_{GS} = - 4.5$ V	- 50 ^d

FEATURES

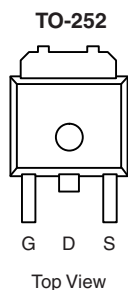
- Halogen-free
- TrenchFET[®] Power MOSFET

APPLICATIONS

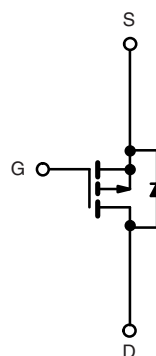
- Load Switch



RoHS
COMPLIANT



Drain Connected to Tab



Ordering Information: SUD50P06-15-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

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Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	- 60	V
Gate-Source Voltage		V _{GS}	± 20	
Continuous Drain Current (T _J = 175 °C)	T _C = 25 °C	I _D	- 50 ^d	A
	T _C = 125 °C		- 27.5	
Pulsed Drain Current		I _{DM}	- 80	
Avalanche Current		I _{AS}	- 50	
Single Pulse Avalanche Energy ^a	L = 0.1 mH	E _{AS}	125	mJ
Power Dissipation	T _C = 25 °C	P _D	113 ^c	W
	T _A = 25 °C		2.5 ^{b, c}	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient ^b	R_{thJA}	15	18	°C/W
		40	50	
Junction-to-Case	R_{thJC}	0.82	1.1	

Notes:

a. Duty cycle ≤ 1 %.

b. When Mounted on 1" square PCB (FR-4 material).

c. See SOA curve for voltage derating.

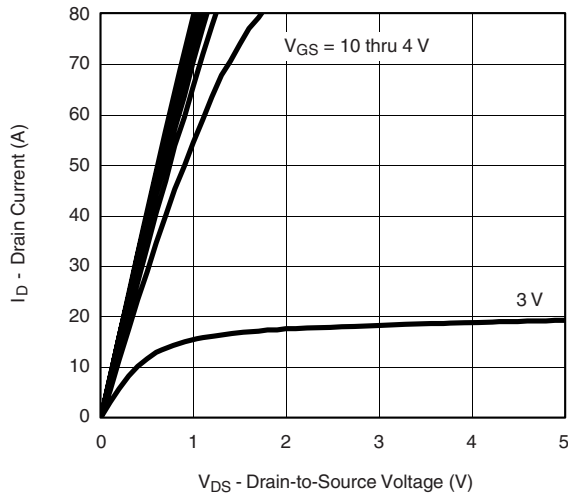
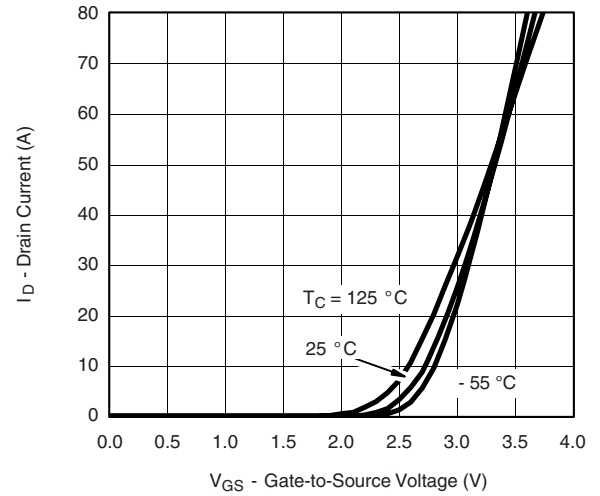
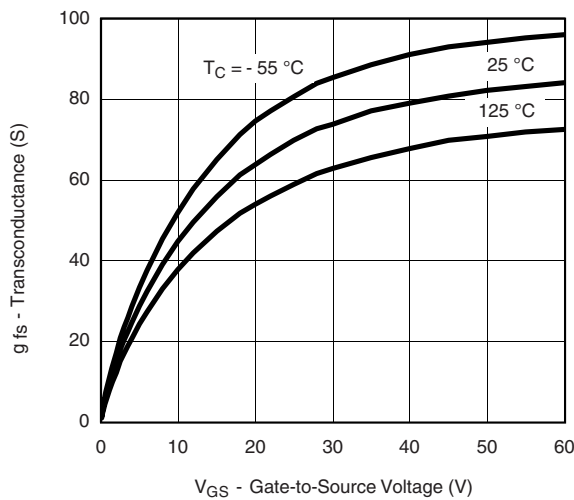
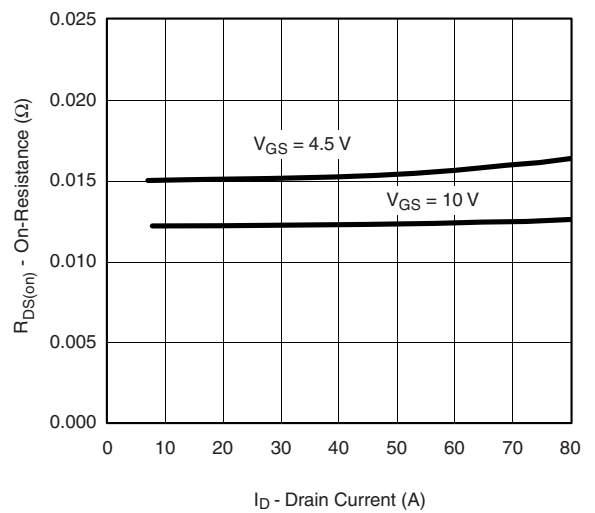
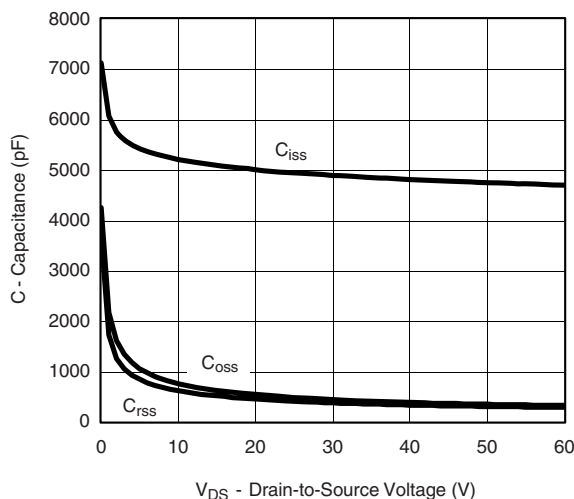
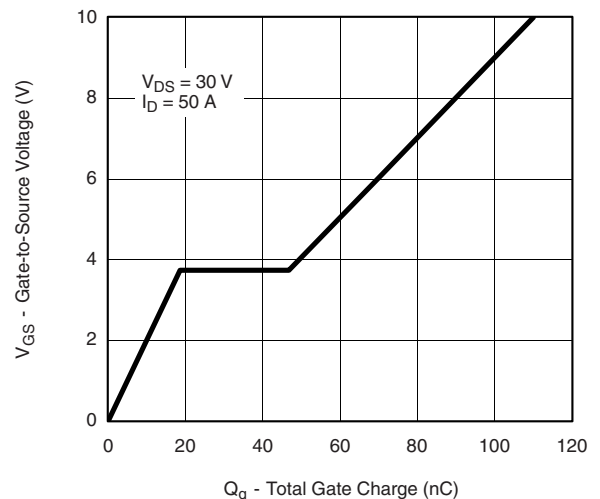
d. Package limited.

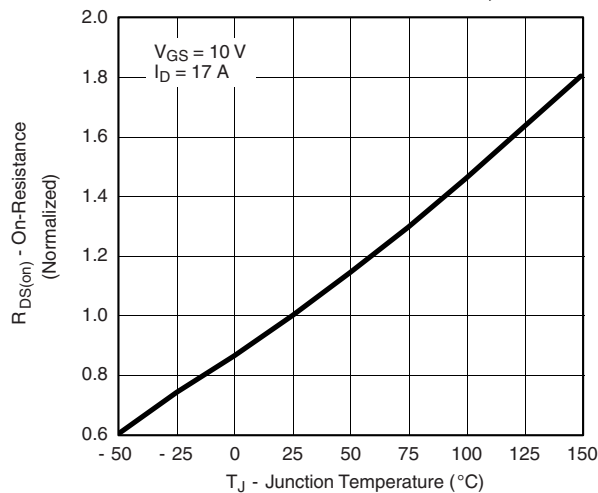
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = - 250 μA	- 60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1		- 3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 60 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 125 °C			- 50	
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 150 °C			- 100	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 50			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 17 A		0.012	0.015	Ω
		V _{GS} = - 10 V, I _D = - 50 A, T _J = 125 °C			0.025	
		V _{GS} = - 10 V, I _D = - 50 A, T _J = 150 °C			0.028	
		V _{GS} = - 4.5 V, I _D = - 14 A			0.020	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 15 V, I _D = - 17 A		61		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = - 25 V, f = 1 MHz		4950		pF
Output Capacitance	C _{oss}			480		
Reverse Transfer Capacitance	C _{rss}			405		
Total Gate Charge ^c	Q _g	V _{DS} = - 30 V, V _{GS} = - 10 V, I _D = - 50 A		110	165	nC
Gate-Source Charge ^c	Q _{gs}			19		
Gate-Drain Charge ^c	Q _{gd}			28		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = - 30 V, R _L = 0.6 Ω I _D ≅ - 50 A, V _{GEN} = - 10 V, R _G = 6 Ω		15	23	ns
Rise Time ^c	t _r			70	105	
Turn-Off Delay Time ^c	t _{d(off)}			175	260	
Fall Time ^c	t _f			175	260	
Source-Drain Diode Ratings and Characteristics T _C = 25 °C ^b						
Continuous Current	I _S				- 50	A
Pulsed Current	I _{SM}				- 80	
Forward Voltage ^a	V _{SD}	I _F = - 50 A, V _{GS} = 0 V		- 1.0	- 1.6	V
Reverse Recovery Time	t _{rr}	I _F = - 50 A, dI/dt = 100 A/μs		45	70	ns

Notes:

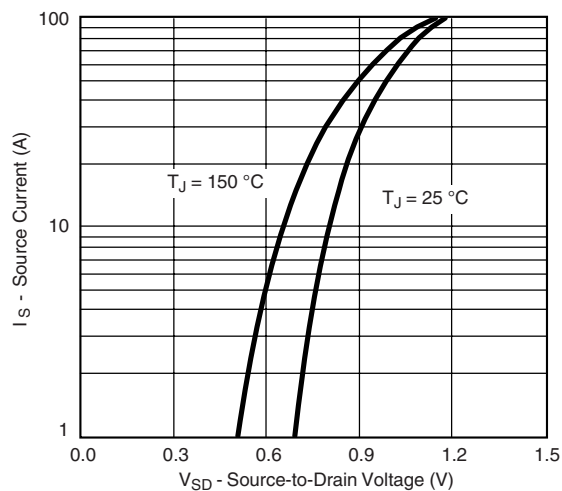
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

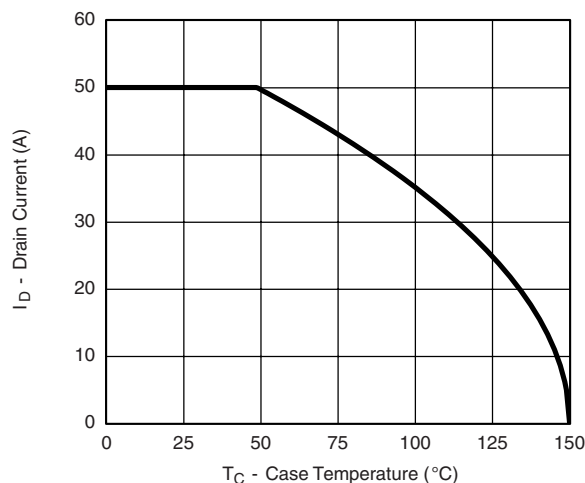
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

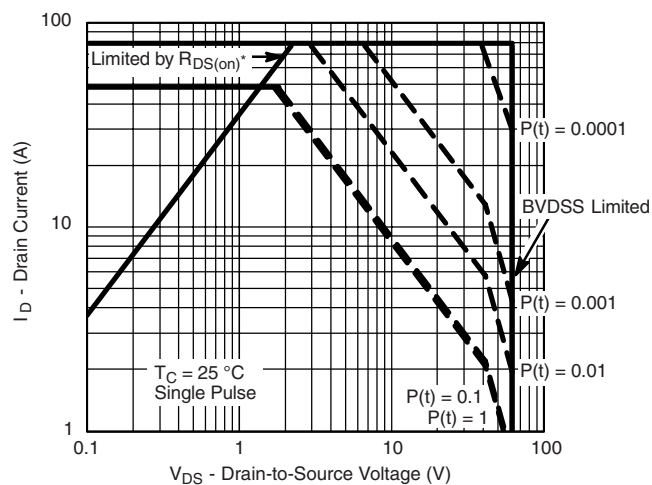
On-Resistance vs. Junction Temperature



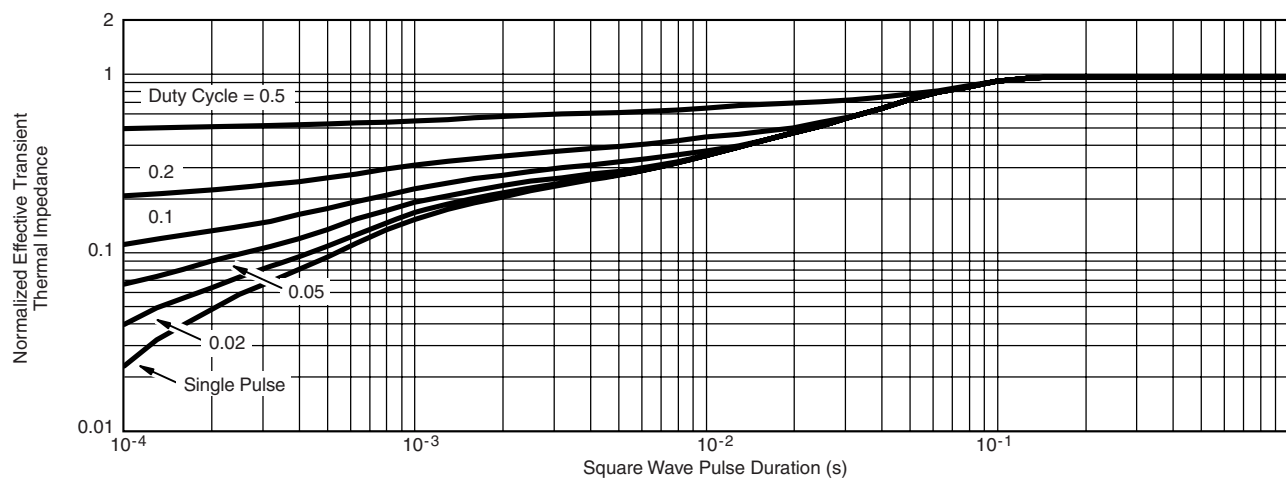
Source-Drain Diode Forward Voltage

THERMAL RATINGS

Drain Current vs. Case Temperature

* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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